



AO4470

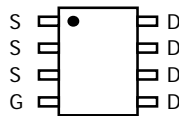
N-Channel Enhancement Mode Field Effect Transistor

General Description

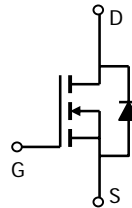
The AO4470 uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity, body diode characteristics and ultra-low gate resistance. This device is ideally suited for use as a low side switch in Notebook CPU core power conversion. *Standard product AO4470 is Pb-free (meets ROHS & Sony 259 specifications). AO4470L is a Green Product ordering option. AO4470 and AO4470L are electrically identical.*

Features

V_{DS} (V) = 30V
 I_D = 18A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 5.5m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 6.2m Ω (V_{GS} = 4.5V)



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	18	A
	$T_A=70^\circ\text{C}$	15	
Pulsed Drain Current ^B	I_{DM}	80	
Power Dissipation	$T_A=25^\circ\text{C}$	3	W
	$T_A=70^\circ\text{C}$	2.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	59	75
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30	34		V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C		0.005	1	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.8	1.12	1.5	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	80			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =18A T _J =125°C		4.2	5.5	mΩ
				6.4	7.4	
		V _{GS} =4.5V, I _D =15A		4.9	6.2	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =18A		102		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.64	1	V
I _S	Maximum Body-Diode Continuous Current				4.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		9130	10500	pF
C _{oss}	Output Capacitance			625		pF
C _{rss}	Reverse Transfer Capacitance			387		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.4	0.8	Ω
SWITCHING PARAMETERS						
Q _{g(4.5V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =18A		72.4	85	nC
Q _{gs}	Gate Source Charge			13.4		nC
Q _{gd}	Gate Drain Charge			16.8		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.83Ω, R _{GEN} =3Ω		11	15	ns
t _r	Turn-On Rise Time			7	11	ns
t _{D(off)}	Turn-Off Delay Time			99	135	ns
t _f	Turn-Off Fall Time			13	19.5	ns
t _{rr}	Body Diode Reverse Recovery Time		I _F =18A, dI/dt=100A/μs		33	40
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =18A, dI/dt=100A/μs		22.2	30	nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t_{θJA} ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

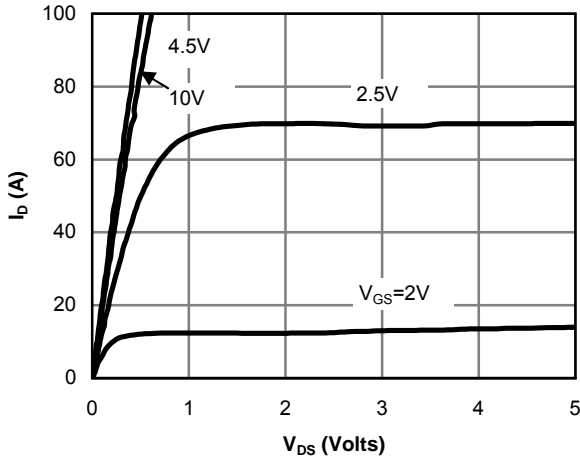


Figure 1: On-Region Characteristics

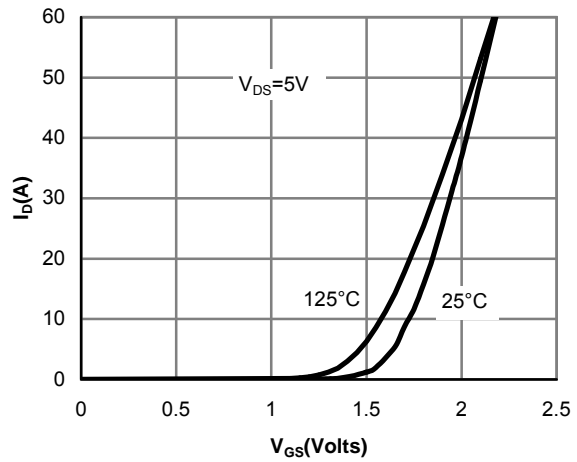


Figure 2: Transfer Characteristics

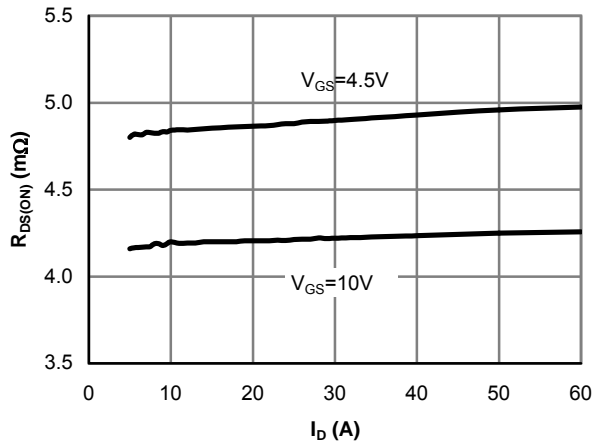


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

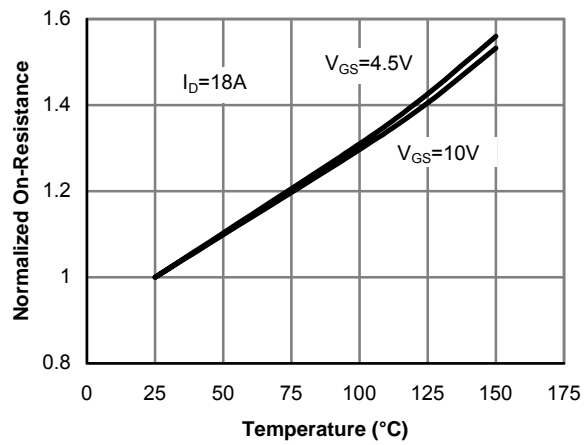


Figure 4: On-Resistance vs. Junction Temperature

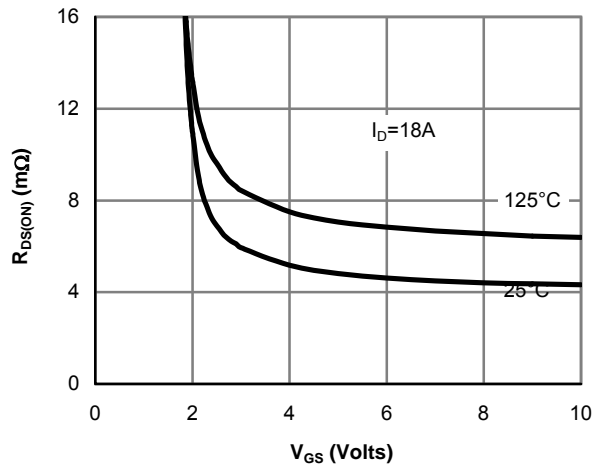


Figure 5: On-Resistance vs. Gate-Source Voltage

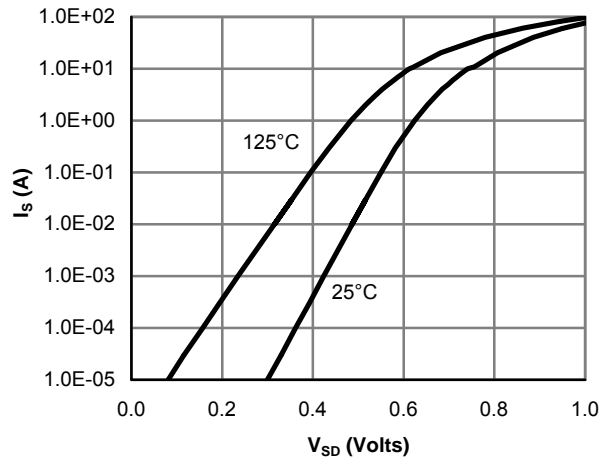


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

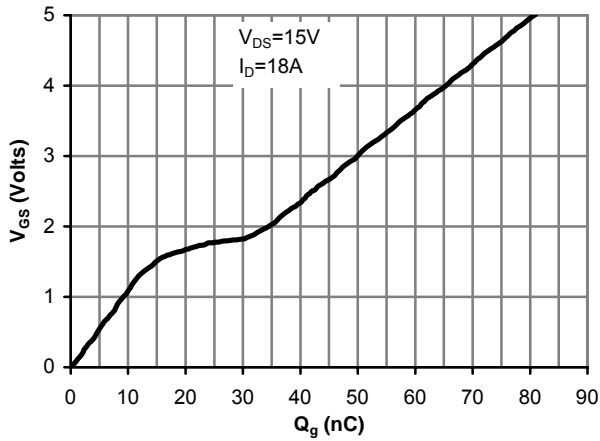


Figure 7: Gate-Charge Characteristics

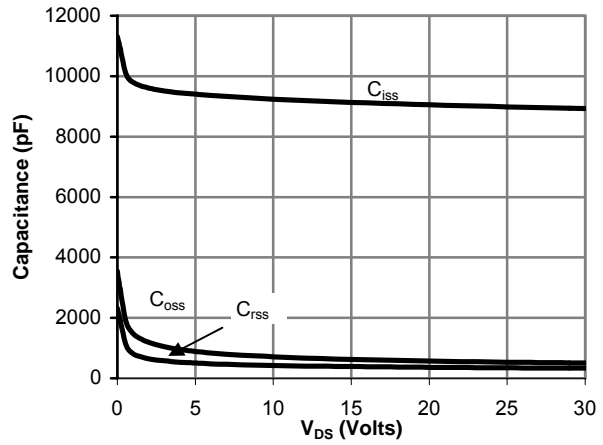


Figure 8: Capacitance Characteristics

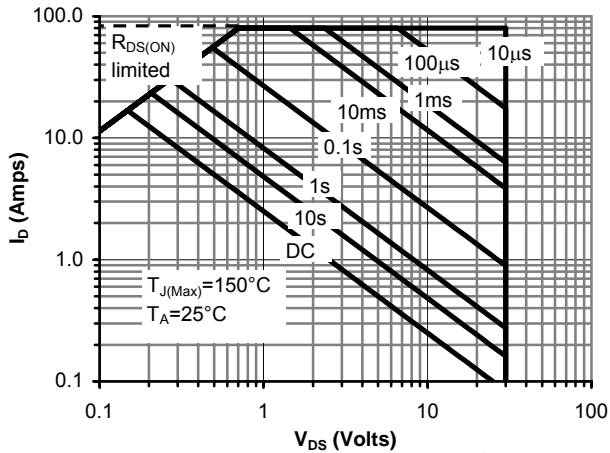


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

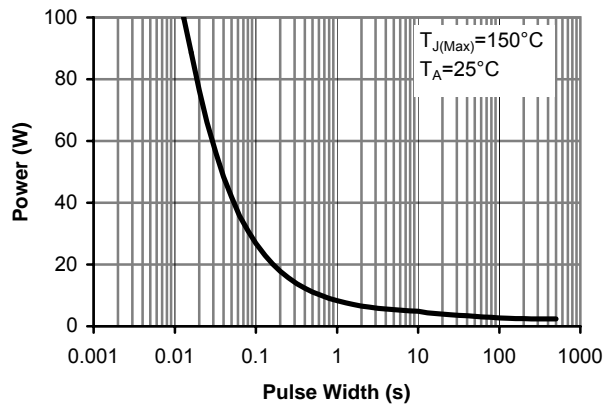


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

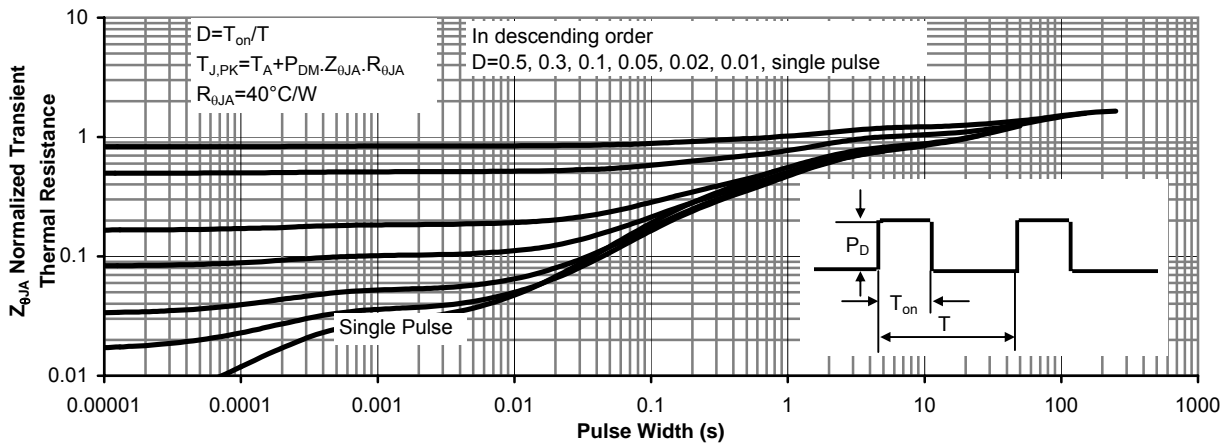


Figure 11: Normalized Maximum Transient Thermal Impedance